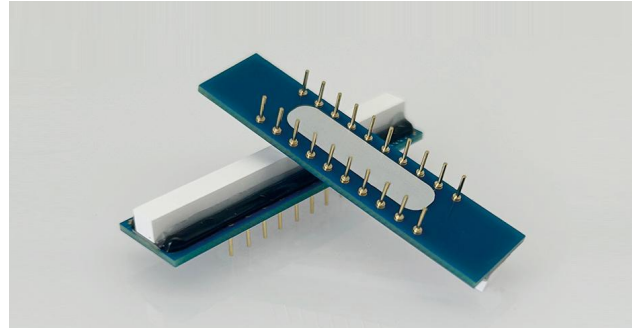


## 1. Overview

EHEC/LEG-2.5P is a linear detector array (LDA) product, made by 16-element front side illumination (FSI) single crystal silicon photodetectors. The silicon photodetector has ultra-low dark current, low terminal capacitance, and high photosensitivity covered a broad spectrum, suitable for varieties of applications



especially in non-destructive X-ray inspection. Wide and narrow board size, coupling with different high performance scintillator, such as GOS screen and CsI scintillator, EHEC/LEG-2.5P can be used directly for single or dual-energy imaging. Well-designed assembly process for easy to integrate and long term reliability.

## 2. Features

- Wide light spectrum range from 350~1100nm with peak response at ~950nm.
- Element size: 2.1(W) x 2.8(H) mm / one element
- Element pitch: 2.5mm (x 16 pixels)
- Mounted on two size of board:
  - 40.2 x 20.0 mm (wide board for low energy)
  - 40.2 x 10.2 mm (narrow board for high energy)
- Support dual energy imaging (when used in an upper and lower two-layer combination)
- Coupled with GOS screen for low energy, and CsI array for high energy. Other scintillators like CWO, GOS ceramic, are optional.
- Detectable energy range: 30 keV to 200 keV.
- Arranging with two or more modules in a row for long size line detector

## 3. Application

- ◆ ..... Car inspection
- ◆ ..... Security inspection
- ◆ ..... Non-destructive testing
- ◆ ..... Thickness measurement
- ◆ ..... Industrial process control
- ◆ ..... Mineral sorting
- ◆ ..... Waste sorting

## 4. Technical Parameter

Si photodiode arrays (no scintillator)				
Parameter	Symbol	Spec.	Unit	
Element pitch	P	2.5	mm	
Element effective width	W	2.1	mm	
Element effective height	H	2.8	mm	
Number of elements	-	16		
Chip length	Length	40.0	mm	
Chip width	Width	5.0	mm	
Electrical and optical characteristics				
Parameter	Symbol	Condition	Spec.	Unit
Spectrum response range	$\lambda$		350-1100	nm
Peak sensitivity wavelength	$\lambda_p$		950	nm
Photosensitivity	S	@550nm	Typ.0.4, Min 0.36	A/W
Dark current	$I_b$	@-10mV	Typ. 7, Max 40	pA
Terminal Capacitance	$C_t$	@0V, f=10kHz	Typ. 55, Max 70	pF
GOS scintillator screen				
Parameter	Symbol	Spec.	Unit	
Thickness of GOS	T	0.35	mm	
Length	L	40.1	mm	
Width	H1	3.4	mm	
CsI scintillator				
Parameter	Symbol	Spec.	Unit	
Length	L	40.1	mm	
Width	H1	3.4	mm	
Thickness	T1	4.0 (for high energy)	mm	
CsI element pitch	P	2.5	mm	
CsI element width	W	2.2	mm	
CsI element height	H	3.0	mm	
CsI element thickness	T	3.0 (for high energy)	mm	
Performance of scintillator				
Parameter	GOS	CsI (TI)	Unit	
Peak emission wavelength	512	550	nm	
Refractive index	2.2	1.79	-	
Decay constant	3	1	us	
Afterglow	0.01	< 1	%@20ms	
Density	7.34	4.51	g/cm <sup>3</sup>	
Sensitivity non-uniformity	±15	±15	%	

## 5. Drawings(unit: mm)

